

**TC74AC11P, TC74AC11F, TC74AC11FN**

**TRIPLE 3-INPUT AND GATE**

The TC74AC11 is an advanced high speed CMOS 3-INPUT AND GATE fabricated with silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

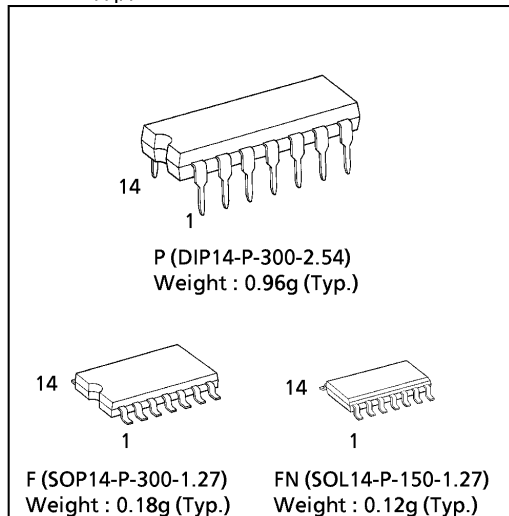
It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The internal circuit is composed of 4 stages including buffer output, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

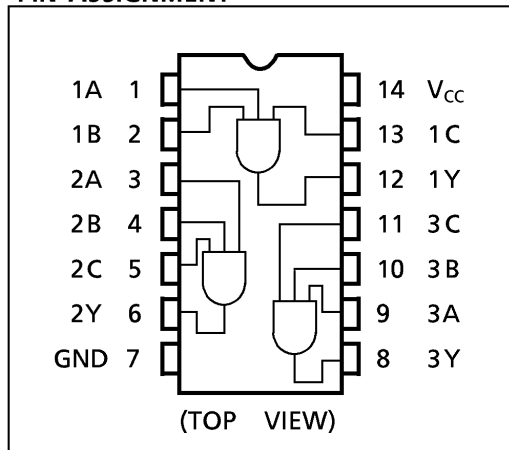
**FEATURES :**

- High Speed..... $t_{pd} = 5.3ns$  (typ.) at  $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 4\mu A$ (Max.) at  $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 24mA$  (Min.)  
 Capability of driving  $50\Omega$  transmission lines.
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC} (opr) = 2V \sim 5.5V$
- Pin and Function Compatible with 74F11

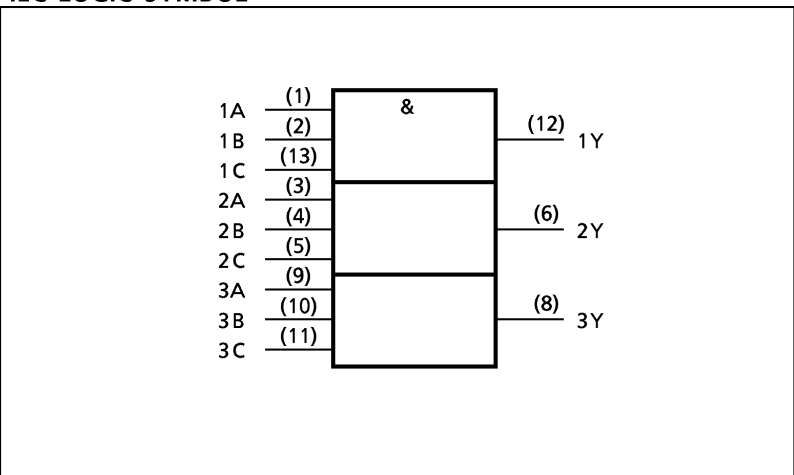
(Note) The JEDEC SOP (FN) is not available in Japan.



**PIN ASSIGNMENT**



**IEC LOGIC SYMBOL**



**TRUTH TABLE**

A	B	C	Y
L	X	X	L
X	L	X	L
X	X	L	L
H	H	H	H

X : Don't Care

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## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7.0	V
DC Input Voltage	$V_{IN}$	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	± 20	mA
Output Diode Current	$I_{OK}$	± 50	mA
DC Output Current	$I_{OUT}$	± 50	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	± 100	mA
Power Dissipation	$P_D$	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	$T_{stg}$	-65~150	°C

\*500mW in the range of  $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$ . From  $T_a = 65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of  $-10\text{mW}/^{\circ}\text{C}$  should be applied up to 300mW.

## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2.0~5.5	V
Input Voltage	$V_{IN}$	0~ $V_{CC}$	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$dt/dV$	0~ 100 ( $V_{CC} = 3.3 \pm 0.3\text{V}$ ) 0~ 20 ( $V_{CC} = 5 \pm 0.5\text{V}$ )	ns / V

## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	$V_{IH}$		2.0	1.50	—	—	1.50	—	V	
			3.0	2.10	—	—	2.10	—		
			5.5	3.85	—	—	3.85	—		
Low - Level Input Voltage	$V_{IL}$		2.0	—	—	0.50	—	0.50	V	
			3.0	—	—	0.90	—	0.90		
			5.5	—	—	1.65	—	1.65		
High - Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$	$I_{OH} = -50\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				3.0	2.9	3.0	—	2.9	—	
				4.5	4.4	4.5	—	4.4	—	
Low - Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 50\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				3.0	—	0.0	0.1	—	0.1	
				4.5	—	0.0	0.1	—	0.1	
Low - Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 12\text{mA}$ $I_{OL} = 24\text{mA}$ $I_{OL} = 75\text{mA}^*$	3.0	—	—	0.36	—	0.44	V
				4.5	—	—	0.36	—	0.44	
				5.5	—	—	—	—	1.65	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	± 0.1	—	± 1.0	$\mu\text{A}$	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	4.0	—	40.0		

\* : This spec indicates the capability of driving  $50\Omega$  transmission lines.

One output should be tested at a time for a 10ms maximum duration.

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AC ELECTRICAL CHARACTERISTICS (  $C_L = 50\text{pF}$ ,  $R_L = 500\ \Omega$ , Input  $t_r = t_f = 3\text{ns}$  )

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Propagation Delay Time	t <sub>pLH</sub>		3.3 ± 0.3	—	8.0	14.0	1.0	16.0	ns
	t <sub>pHL</sub>		5.0 ± 0.5	—	6.0	9.0	1.0	10.2	
Input Capacitance	C <sub>IN</sub>		—	5	10	—	10	pF	
Power Dissipation Capacitance	C <sub>PD</sub> (1)		—	63	—	—	—		

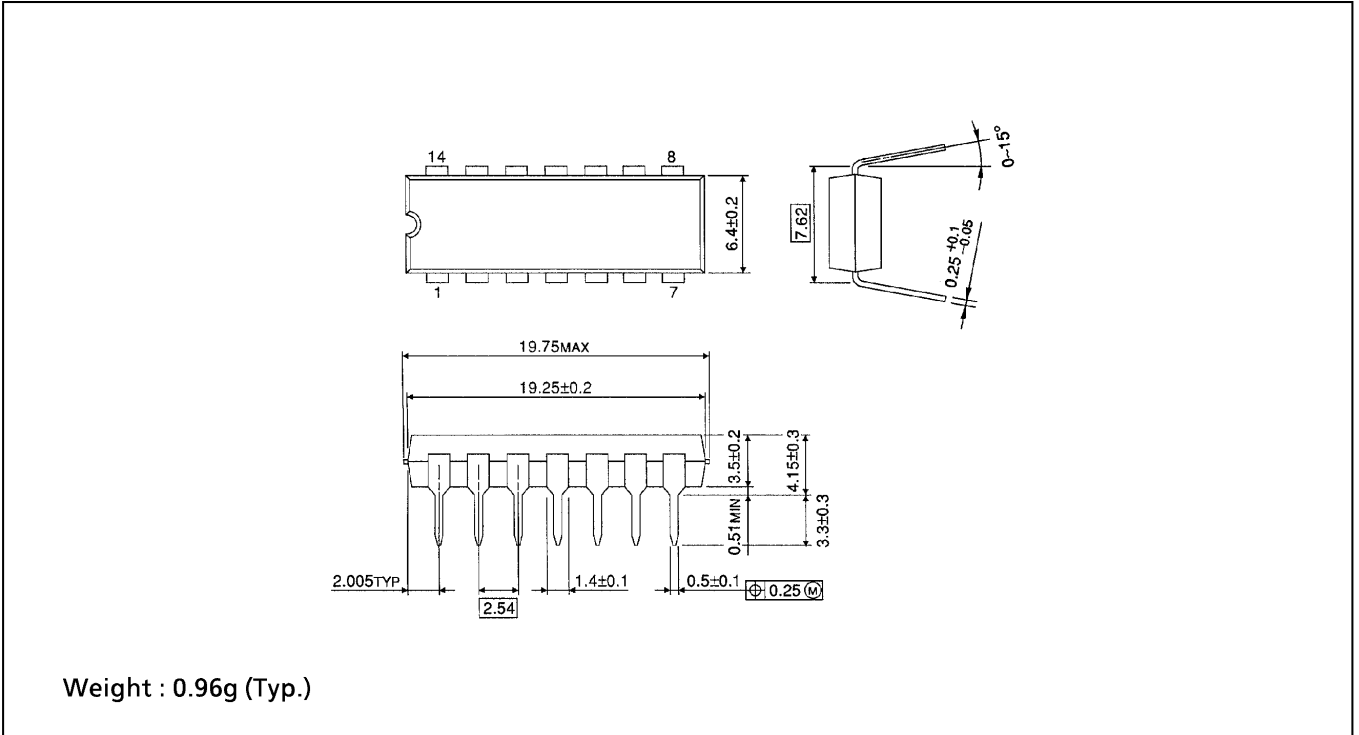
Note (1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 3 \text{ (per Gate)}$$

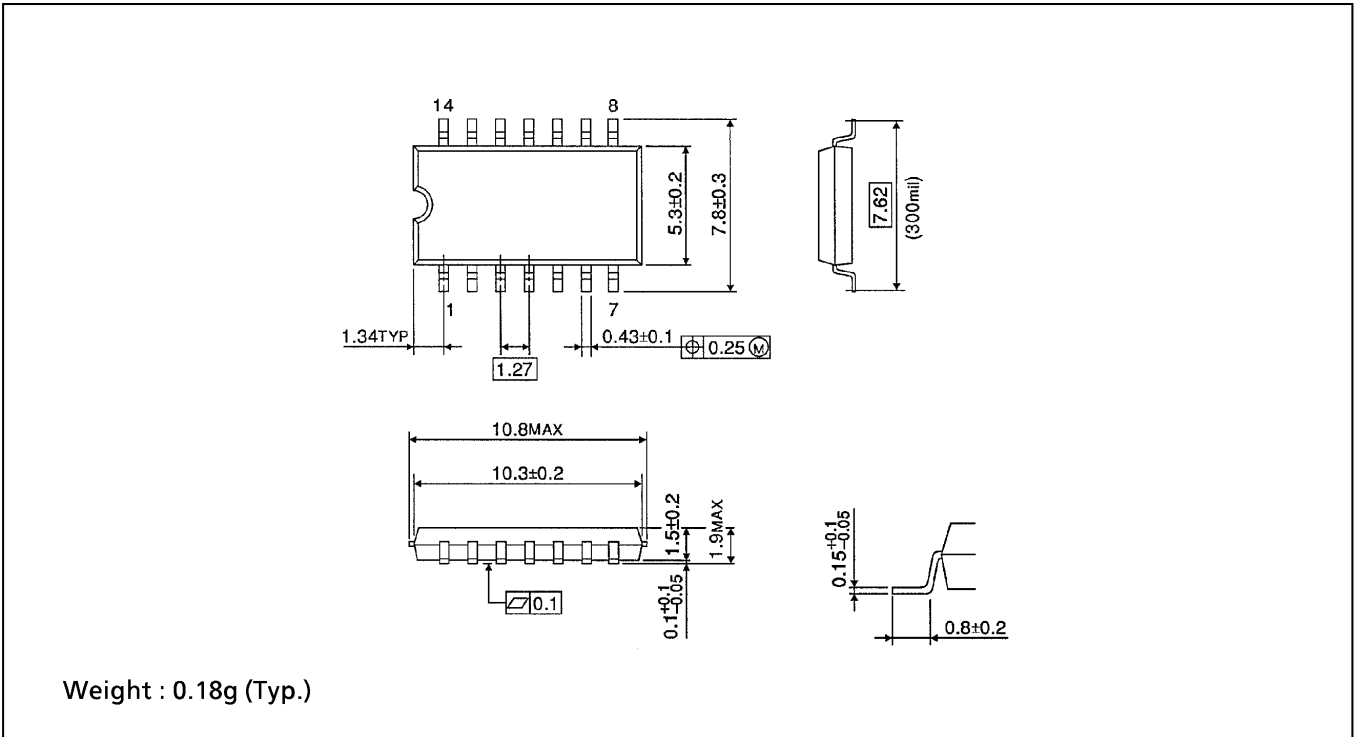
DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

Unit in mm



SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

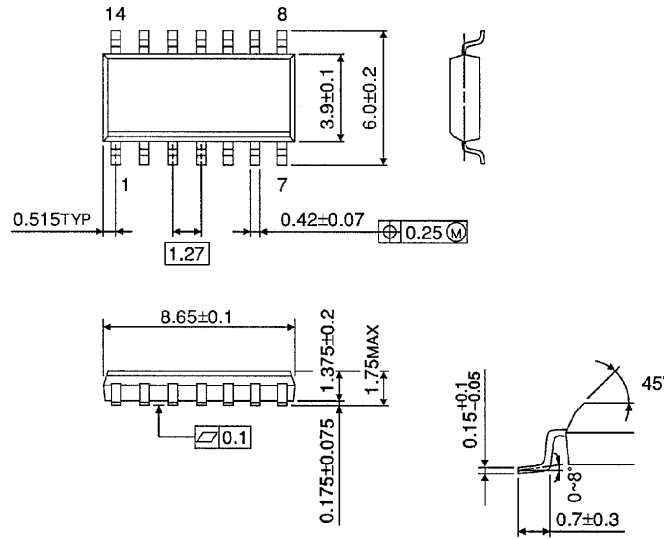
Unit in mm



**SOP 14PIN (150mil BODY) OUTLINE DRAWING (SOL14-P-150 -1.27)**

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.12g (Typ.)